

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SC1905

DESCRIPTION

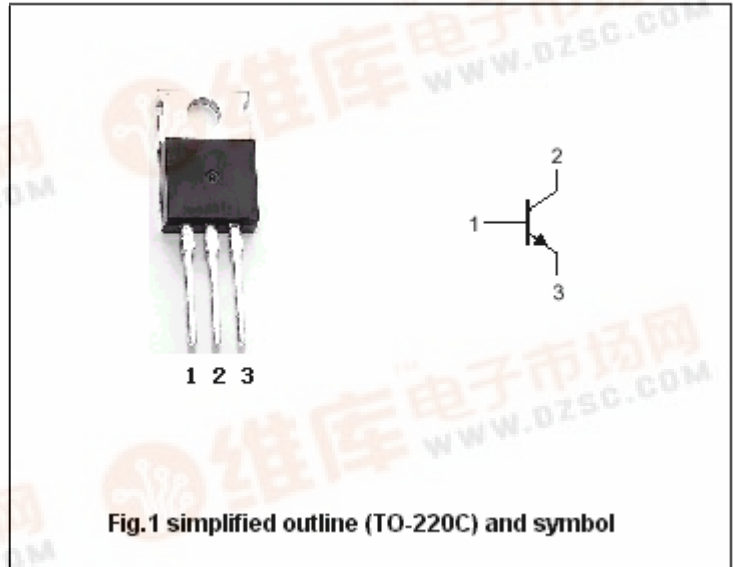
- With TO-220C package
- High breakdown voltage
- Large collector power dissipation

APPLICATIONS

- Color TV horizontal deflection driver

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	350	V
V _{CEO}	Collector-emitter voltage	Open base	300	V
V _{EBO}	Emitter-base voltage	Open collector	7.5	V
I _C	Collector current		200	mA
I _{CM}	Collector current-peak		400	mA
P _C	Collector power dissipation	T _C =25	15	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =5mA ; I _B =0	300			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =100 μ A ; I _E =0	350			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =100 μ A ; I _C =0	7.5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =50mA; I _B =5mA			1.0	V
I _{CBO}	Collector cut-off current	V _{CB} =200V ; I _E =0			2	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			2	μ A
h _{FE}	DC current gain	I _C =10m A ; V _{CE} =10V	40		250	
f _T	Transition frequency	I _C =10m A ; V _{CE} =30V	50			MHz
C _{OB}	Output capacitance	I _E =0 ; V _{CB} =50V; f=1MHz			4.5	pF
t _{stg}	Storage time	I _C =100mA; I _{B1} =10mA; I _{B2} =0	5		7.5	μ s

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PACKAGE OUTLINE

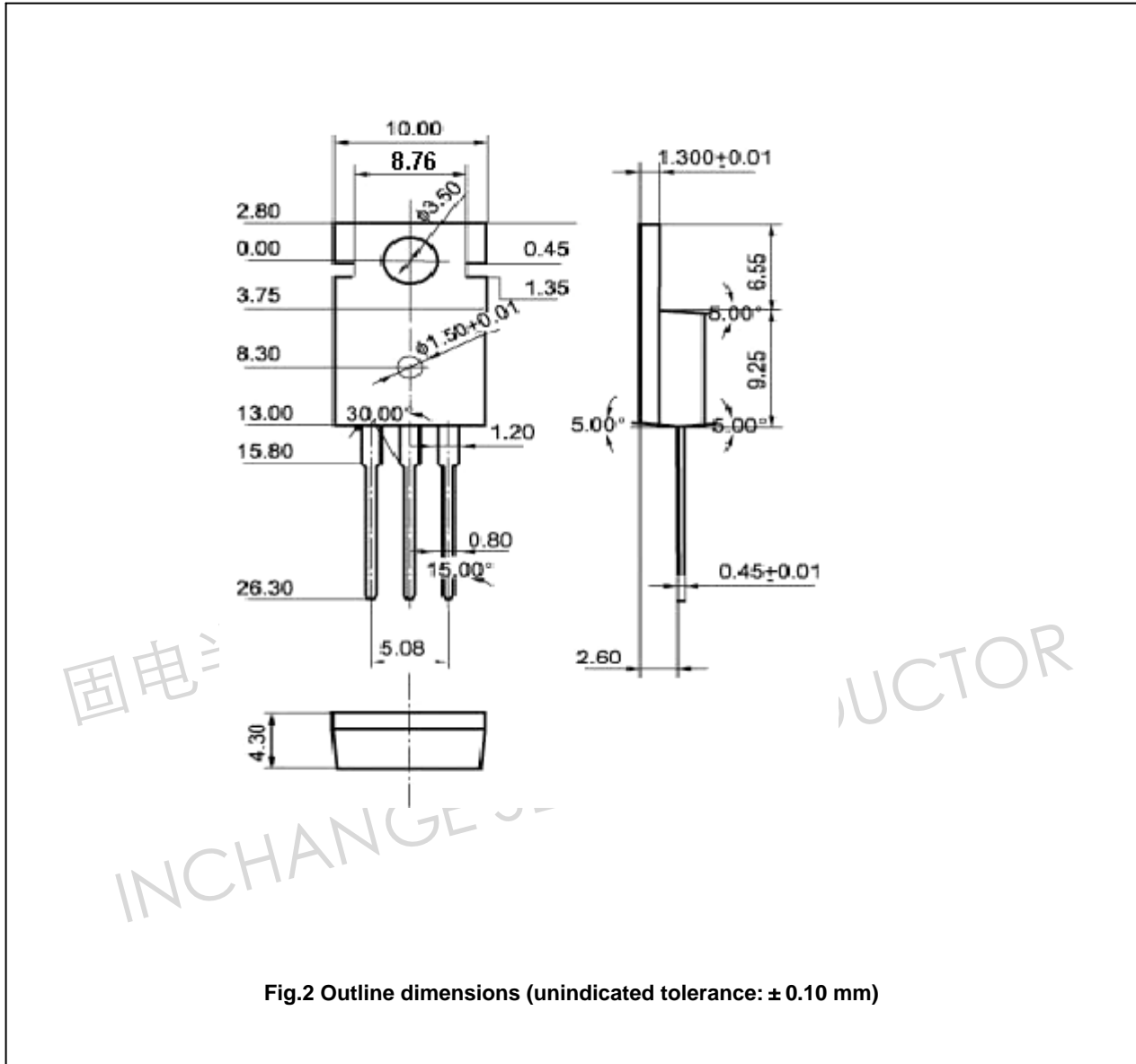


Fig.2 Outline dimensions (unindicated tolerance: ± 0.10 mm)